

**OGOSH53USA**

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: )  
Yuichiro Shindo ) Examiner:  
Application No.: ) Group Art Unit:  
Corresponding International Filing No.: )  
**PCT/JP2004/015777** )  
Filed: Herewith )  
For: HIGH PURITY HAFNIUM, )  
TARGET AND THIN FILM )  
COMPRISING SAID HIGH )  
PURITY HAFNIUM, AND )  
METHOD FOR PRODUCING )  
HIGH PURITY HAFNIUM )

Mail Stop PCT  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

**SECOND PRELIMINARY AMENDMENT**

Sir:

Please amend the above-identified patent application as follows.

**Amendments to the Specification** begin on page two of this paper.

**Amendments to the Claims** are reflected in the listing of claims which begins on page three of this paper.

**Remarks** begin on page five of this paper.